



ELECTRONICS, INC.
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NTE2585 Silicon NPN Transistor High Voltage Amplifier

Features:

- High Breakdown Voltage
- Low Output Capacitance
- High Reliability
- Intended for High-Density Mounting (Suitable for Sets Whose Height is Restricted)

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector Base Voltage, V_{CBO}	800V
Collector Emitter Voltage, V_{CEO}	800V
Emitter Base Voltage, V_{EBO}	7V
Collector Current, I_C	
Continuous	20mA
Peak	60mA
Collector Power Dissipation, P_C	1.65W
Operating Junction Temperature, T_J	+150°C
Storage Temperature Range, T_{stg}	-55° to +150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800V, I_E = 0$	-	-	1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	-	-	1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 2mA$	20	-	50	
		$V_{CE} = 5V, I_C = 10mA$	10	-	-	
Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 2mA$	-	40	-	MHz
Output Capacitance	C_{ob}	$V_{CB} = 100V, f = 1MHz$	-	1.6	-	pF
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 2mA$	-	-	1.0	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10mA, I_B = 2mA$	-	-	1.5	V
Collector Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	800	-	-	V
Collector Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	800	-	-	V
Emitter Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	7	-	-	V

